### **European School on Magnetism 2009**

### FШF



# Inhomogeneities in magnetic systems



Inhomogeneous magnetic systems: control and applications

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### Control over magnetic ions aggregation





#### e.g. vertical alignement of InAs QDs in GaAs





#### PbSe/Pb<sub>1-x</sub>Eu<sub>x</sub>Te superlattices

G.Springholz *et al.* Science **282**, 734 [1998] **Review**: J.Stangl, V.Holý, G.Bauer, Rev.Mod.Phys. **76**, 689 [2004]

### Ways to control the aggregation of TM

### 1] growth rate

### 2] growth temperature

### co-doping with donors or acceptors

T. Dietl, Nature Mat. 5, 673 [2006]

L.H. Ye and A. Freeman, Phys.Rev. B 73, 81304 [2006]

### Why aggregation of magnatic ions?

#### Unique aspect of our material systems:

- d-levels in the gap
- contribute to the bonding
- foster attractive force between magnetic ions
- kinetic barrier to the formation of ferromagnetic nanocrystals

#### By changing the valency

- modification of the attractive force
- influence on the magnetic ions aggregation

### 3] co-doping with donors or acceptors

A. Bonanni et al. Phys.Rev.Lett. 101, 135502 [2008]

### Control by co-doping

- TM-related states reside in the host band gap
- charge state and intersite Coulomb repulsion can be changed by **co-doping** with shallow impurities
- the Coulomb repulsion between TM ions hinders spinodal decomposition



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### (Zn,Cr)Te – effect of codoping on Cr distribution



### Effect of Si-doping

Quenching of ferromagnetic response



### Effect of Si-doping [on secondary phases]

**Quenching of ferromagnetic response** 



**Reduction/dissolution of secondary phases** 

### Effect of Si-doping [on chemical decomposition]



#### Si doping – effect on Fe charge state



M. Rovezzi, ..AB, ...Phys.Rev. B 79, 195209 [2009]

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### Co-doping and TM aggregation

#### summary



A. Bonanni et al. Phys.Rev.Lett. 101, 135502 [2008]

### Outlook

### Outlook: self-organized nanocolumns



M. Jamet et al., Nature Mat. 5, 653 [2006]

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M. Jamet et al., Nature Mat. 5, 653 [2006]



L. Gu et al., JMMM 290, 1395 [2005]

### Self-organized nanomagnets in semiconductors



#### **Domain walls for 3D memories**

electric current induces the shift of magnetic regions along a wire

#### HD does not need to spin

#### increased data storage and speed

G. Meier et al., Phys.Rev.Lett. 98, 187202 [2007]

Unclear:

how to fabricate dense arrays of required nanocolumns

self-organized nanocolumns in DMS [?]

### Spin-battery – GaAs:MnAs







P. Nam-Hai et al., Nature 458, 489 [2009]



### Functionalities

 nanometallization: nanoelectronics, optoelectronics, plasmonics

- large magnetotransport effects field sensors
- large magnetooptical effects optical isolators, tunable photonic crystals
- spintronic structures
   high density MRAMs/race track memories/logic
- spin battery

 large spin entropy thermoelectricity P. Nam-Hai et al., Nature 458, 489 [2009]

H. Katayama-Yoshida *et al.,* Jpn.J.Appl.Phys **46**, L777 [2007]

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